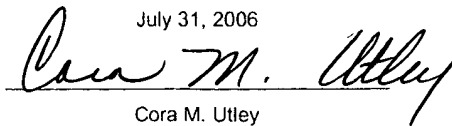




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July 31, 2006


Cora M. Utley

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor: Christopher L. Chua Date: July 31, 2006
Serial No.: 09/933,960 Group: 2828
Filed: August 20, 2001 Examiner: Menefee, James A.
Title: **METHOD AND STRUCTURE FOR ELIMINATING POLARIZATION
INSTABILITY IN Laterally-Oxidized VCSELS**

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

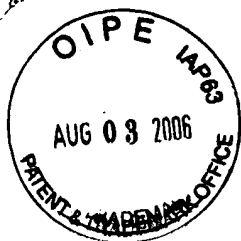
Sir:

REQUEST FOR CONTINUED EXAMINATION COMMENTS

Applicant filed an information disclosure statement on May 17, 2006 (hereinafter IDS). Applicant's representative was unaware at the time that the Examiner had already mailed out a Notice of Allowance. In order to have the IDS considered by the Examiner, Applicant hereby requests that prosecution be reopened and thus submits a Request For Continued Examination along with the required RCE fees.

Respectfully submitted,


Kent Chen
Attorney for Applicant(s)
Registration No. 39,630
(310) 333-3663
July 31, 2006



CERTIFICATE OF MAILING

Attorney Docket No.

97005-US-DIV1

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on 7/31/2006

Date

Cora M. Utley
Cora M. Utley

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of Christopher L. Chua et al.

Group Art Unit: 2828

Application No.: 09/933,960

Examiner: James A. Menefee

Filed: August 20, 2001

Confirmation No.: 9309

For: METHOD AND STRUCTURE FOR ELIMINATING POLARIZATION INSTABILITY IN LATERALLY - OXIDIZED VCSELS

Mail Stop: Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) and information listed on the attached PTO-1449 Form. One legible copy of each is attached to the PTO-1449 Form, except for U.S. Patents, or published or IFW (Image File Wrapper) available U.S. applications. It is respectfully requested that the references and information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of the above application (excluding an RCE), **OR** (b) before the mailing date of a first Office Action on the merits (including an RCE). *No certification or fee is required.*
- ☐ 2. This Information Disclosure Statement is being filed more than three months after the U.S. filing date **AND** after the date of the first Office Action on the merits, but before the mailing date of a Final Rejection, Notice of Allowance, or other action that closes prosecution. Please debit Xerox Corporation Deposit Account 24-0025 in the amount of \$180.00 in payment of the fee under 37 C.F.R. 1.17(p). *(A copy of this paper is attached.)*
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Application No. 09/933,960

- ☐ b. I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 C.F.R. §1.56(c), more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. 1.97(e)(2)
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- ☐ 5. Per 37 C.F.R. 1.98(a)(3), a concise explanation of the relevance of each of any submitted item that is NOT in the English language is either enclosed herewith, or incorporated in the application specification.
- ☐ 6. A copy of an English language version of an above-referenced counterpart foreign application search report is attached.
- ☐ 7. Copies of some or all of the subject references were cited or submitted to the Office in related parent Application No. _____, filed _____, which is relied upon under 35 U.S.C. §120. Thus, copies of those references are not attached (except for copies of cited pending applications). 37 C.F.R. §1.98(d).



Kent M. Chen

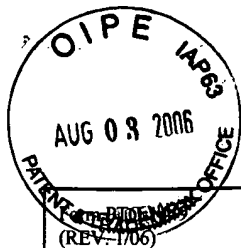
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Sheet 1 of 4

US Dept. of Commerce PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				ATTY DOCKET NO. 97005-US-DIV1	APPLICATION NO. 09/933,960
				APPLICANT(S) Robert L. THORNTON	
				FILING DATE August 20, 2001	GROUP 2828
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EXAMINER		DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		

Date: July 27, 2006